

# SANYO Semiconductors

DATA SHEET

An ON Semiconductor Company

# N-Channel Silicon MOSFET FW216A — General-Purpose Switching Device **Applications**

# **Features**

- ON-resistance Nch :  $R_{DS}(on)1=49m\Omega$  (typ.)
- 4.0V drive
- · Halogen free compliance

# **Specifications**

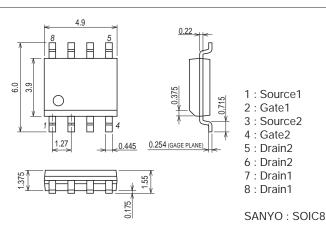
#### Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V <sub>DSS</sub>		35	V
Gate-to-Source Voltage	VGSS		±20	V
Drain Current (DC)	ID		4.5	А
Drain Current (PW≤10µs)	IDP	Duty cycle≤1%	18	А
Allowable Power Dissipation	PD	When mounted on ceramic substrate (2000mm <sup>2</sup> ×0.8mm) 1unit, PW≤10s	1.6	W
Total Dissipation	PT	When mounted on ceramic substrate (2000mm <sup>2</sup> ×0.8mm), PW≤10s	2.2	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

### Package Dimensions

#### unit : mm (typ)

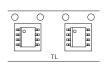
7072-001



#### **Product & Package Information** : SOIC8

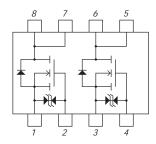
- Package • JEITA, JEDEC
  - : SC-87, SOT96
- Minimum Packing Quantity : 2,500 pcs./reel

## Packing Type : TL





# **Electrical Connection**



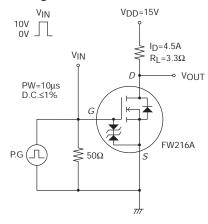
#### SANYO Semiconductor Co., Ltd. http://semicon.sanyo.com/en/network

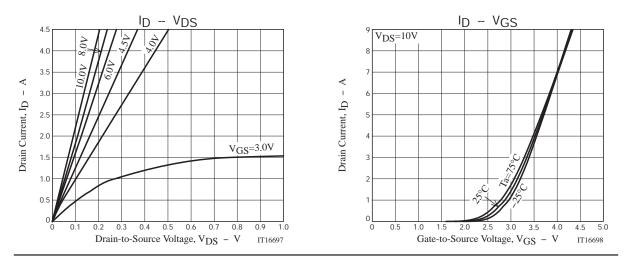
31412 TKIM/20112PA TKIM TC-00002686 No. A0176-1/4

#### Electrical Characteristics at Ta=25°C

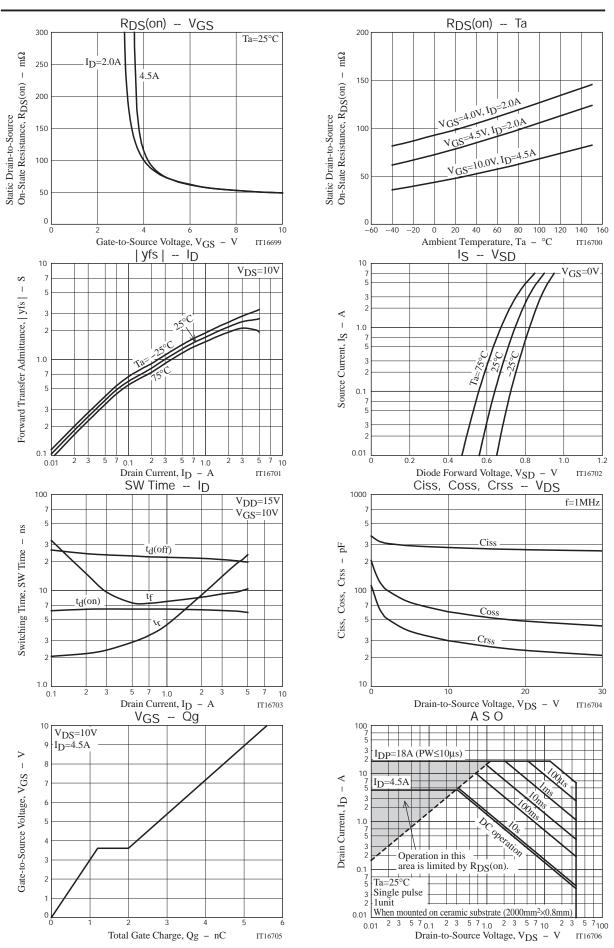
Parameter	Symbol	Conditions	Ratings			11-14
			min	typ	max	Unit
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	35			V
Zero-Gate Voltage Drain Current	IDSS	VDS=35V, VGS=0V			1	μΑ
Gate-to-Source Leakage Current	IGSS	VGS=±16V, VDS=0V			±10	μΑ
Cutoff Voltage	V <sub>GS</sub> (off)	V <sub>DS</sub> =10V, I <sub>D</sub> =1mA	1.5		2.5	V
Forward Transfer Admittance	yfs	V <sub>DS</sub> =10V, I <sub>D</sub> =4.5A		2.6		S
Static Drain-to-Source On-State Resistance	R <sub>DS</sub> (on)1	ID=4.5A, VGS=10V		49	64	mΩ
	R <sub>DS</sub> (on)2	ID=2A, VGS=4.5V		80	112	mΩ
	R <sub>DS</sub> (on)3	ID=2A, VGS=4.0V		100	140	mΩ
Input Capacitance	Ciss			280		pF
Output Capacitance	Coss	V <sub>DS</sub> =10V, f=1MHz		60		pF
Reverse Transfer Capacitance	Crss			30		pF
Turn-ON Delay Time	t <sub>d</sub> (on)			6		ns
Rise Time	tr			21		ns
Turn-OFF Delay Time	t <sub>d</sub> (off)	See specified Test Circuit.		20		ns
Fall Time	t <sub>f</sub>	1		10		ns
Total Gate Charge	Qg			5.6		nC
Gate-to-Source Charge	Qgs	V <sub>DS</sub> =10V, V <sub>GS</sub> =10V, I <sub>D</sub> =4.5A		1.2		nC
Gate-to-Drain "Miller" Charge	Qgd	1		0.8		nC
Diode Forward Voltage	VSD	IS=4.5A, VGS=0V		0.85	1.2	V

#### Switching Time Test Circuit



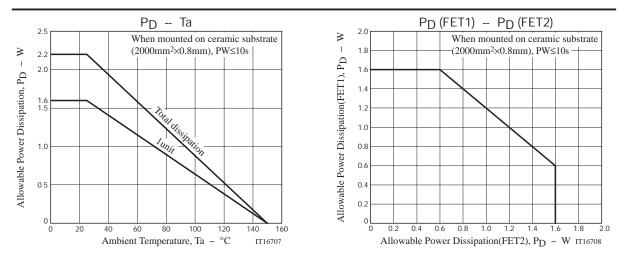


FW216A



Downloaded from Elcodis.com electronic components distributor

No. A0176-3/4



Note on usage : Since the FW216A is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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